

## PolarP™ Power MOSFET

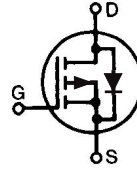
## IXTK170P10P IXTX170P10P

$$V_{DSS} = -100V$$

$$I_{D25} = -170A$$

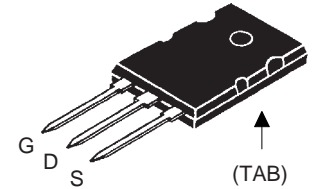
$$R_{DS(on)} \leq 12m\Omega$$

P-Channel Enhancement Mode  
Avalanche Rated

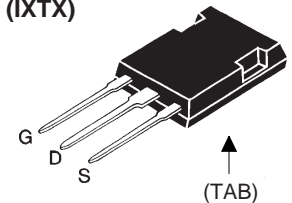


Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	-100	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	-100	V
$V_{GSS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ C$	-170	A
$I_{LRMS}$	Lead Current Limit, RMS	-160	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	-510	A
$I_A$	$T_C = 25^\circ C$	-170	A
$E_{AS}$	$T_C = 25^\circ C$	3.5	J
$dV/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	10	V/ns
$P_D$	$T_C = 25^\circ C$	890	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
$T_{SOLD}$	Plastic Body for 10s	260	$^\circ C$
$M_d$	Mounting Force (PLUS247) Mounting Forque (TO-264)	20..120 / 4.5..27 1.13 / 10	N/lb. Nm/lb.in.
<b>Weight</b>	PLUS247 TO-264	6 10	g g

TO-264 (IXTK)



PLUS247 (IXTX)



G = Gate      D = Drain  
S = Source    TAB = Drain

### Features

- International Standard Packages
- Rugged PolarP™ Process
- High Current Handling Capability
- Fast Intrinsic Diode
- Avalanche Rated
- Low Package Inductance

### Advantages

- Easy to Mount
- Space Savings
- High Power Density

### Applications

- High-Side Switches
- Push Pull Amplifiers
- DC Choppers
- Automatic Test Equipment
- Current Regulators

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = -250\mu A$	-100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = -1mA$	-2.0		-4.0 V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ C$			-50 $\mu A$ -250 $\mu A$
$R_{DS(on)}$	$V_{GS} = -10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1			12 m $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = -10\text{V}$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1	35	58	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = -25\text{V}$ , $f = 1\text{MHz}$		12.6	nF
$C_{oss}$			4190	pF
$C_{rss}$			930	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = -10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$ $R_G = 1\Omega$ (External)		32	ns
$t_r$			75	ns
$t_{d(off)}$			82	ns
$t_f$			45	ns
$Q_{g(on)}$	$V_{GS} = -10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$		240	nC
$Q_{gs}$			45	nC
$Q_{gd}$			120	nC
$R_{thJC}$			0.14	$^\circ\text{C/W}$
$R_{thCS}$		0.15		$^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_s$	$V_{GS} = 0\text{V}$			-170 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			-680 A
$V_{SD}$	$I_F = -85\text{A}$ , $V_{GS} = 0\text{V}$ , Note 1			-3.3 V
$t_{rr}$	$I_F = -85\text{A}$ , $-di/dt = -100\text{A}/\mu\text{s}$		176	ns
$Q_{RM}$			1.25	$\mu\text{C}$
$I_{RM}$	$V_R = -50\text{V}$ , $V_{GS} = 0\text{V}$		-14.2	A

Note 1: Pulse Test,  $t \leq 300\mu\text{s}$ ; Duty Cycle,  $d \leq 2\%$ .

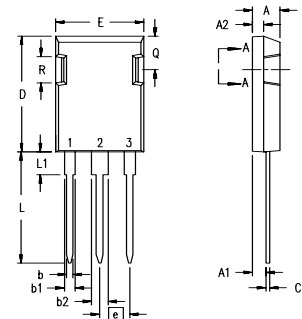
### TO-264 (IXTK) Outline



- 1 - GATE
- 2, 4 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

### PLUS 247™ (IXTX) Outline



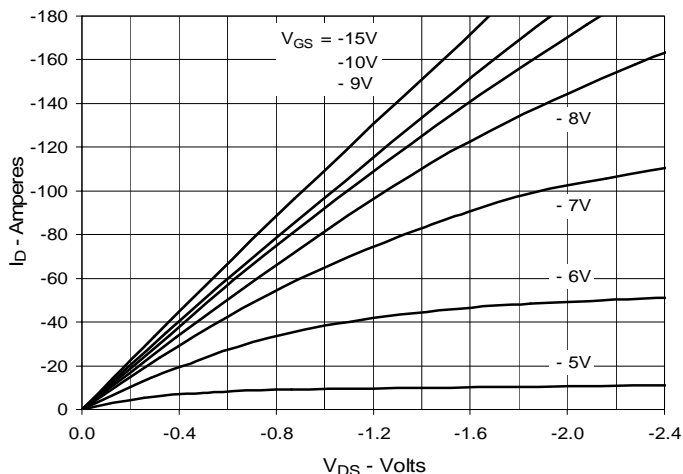
- Terminals: 1 - Gate
- 2 - Drain (Collector)
- 3 - Source (Emitter)
- 4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A <sub>1</sub>	2.29	2.54	.090	.100
A <sub>2</sub>	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b <sub>1</sub>	1.91	2.13	.075	.084
b <sub>2</sub>	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

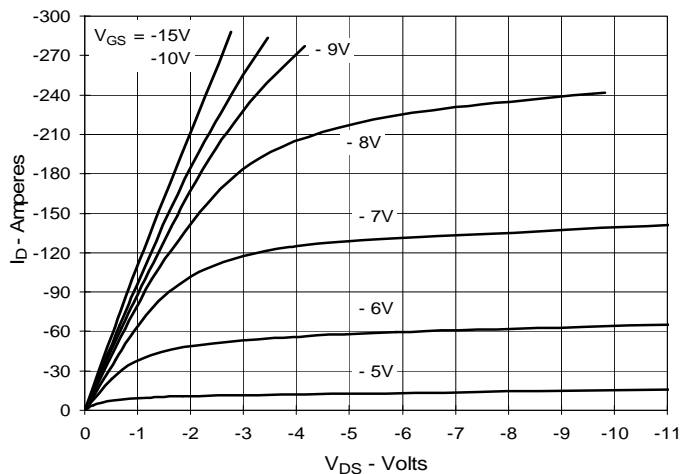
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

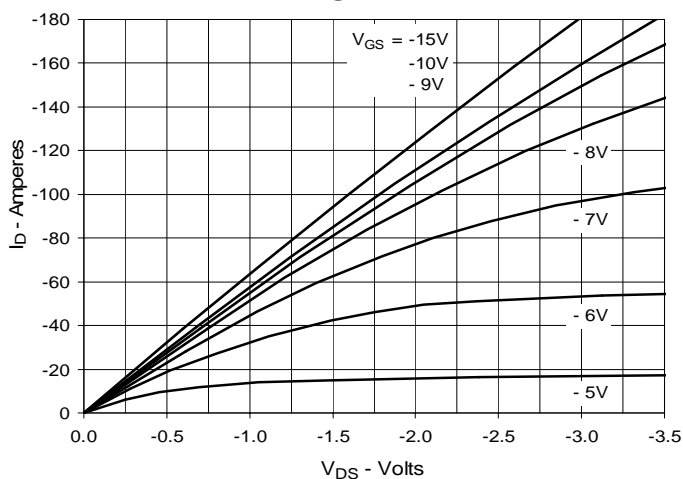
**Fig. 1. Output Characteristics @ 25°C**



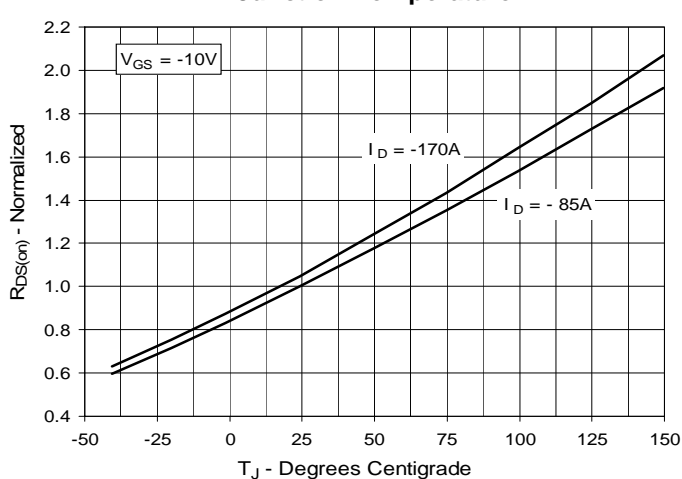
**Fig. 2. Extended Output Characteristics @ 25°C**



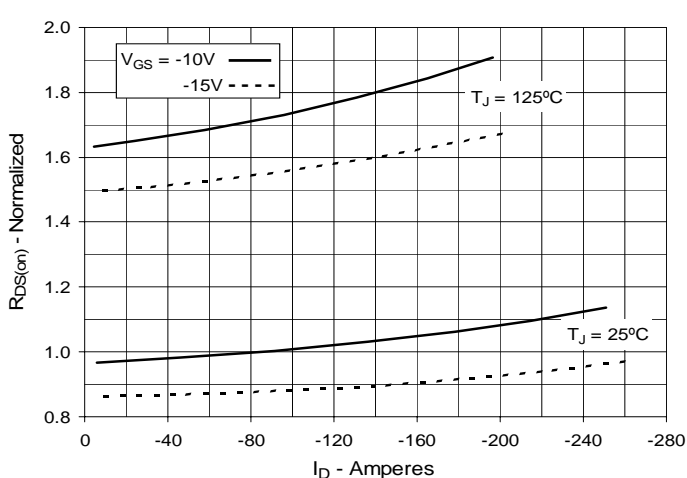
**Fig. 3. Output Characteristics @ 125°C**



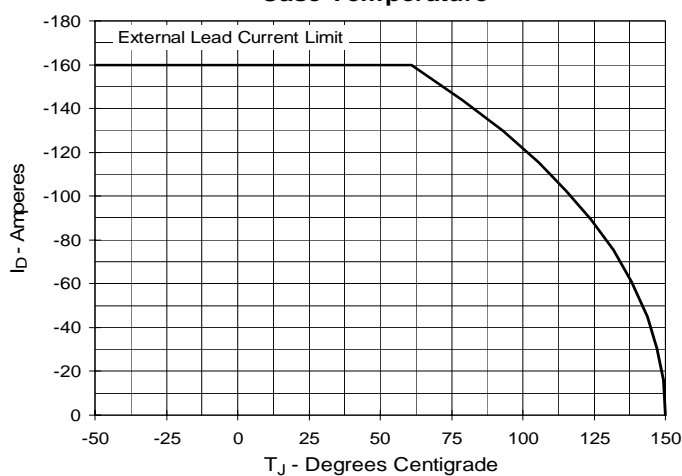
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = -85A$  vs. Junction Temperature**



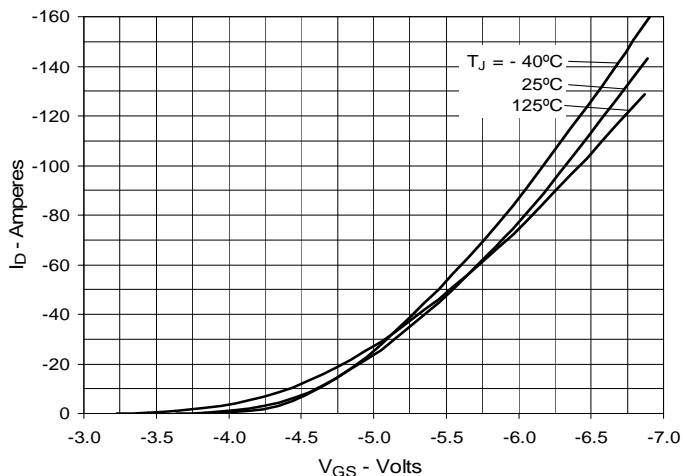
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = -85A$  vs. Drain Current**



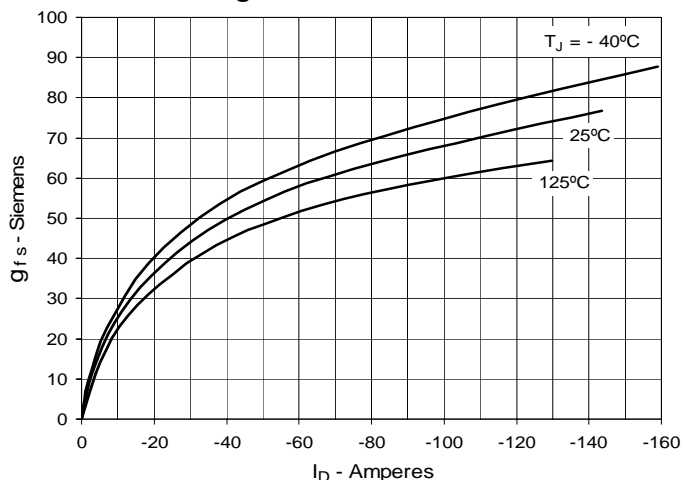
**Fig. 6. Maximum Drain Current vs. Case Temperature**



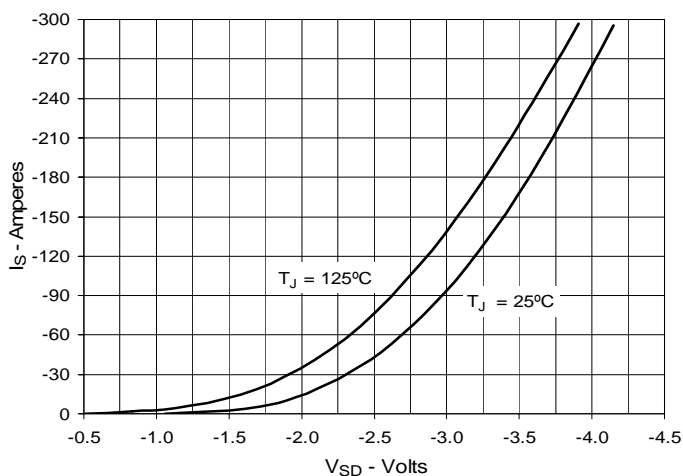
**Fig. 7. Input Admittance**



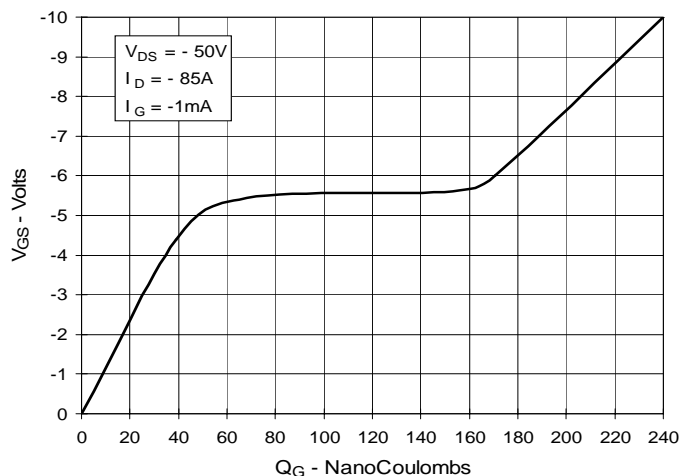
**Fig. 8. Transconductance**



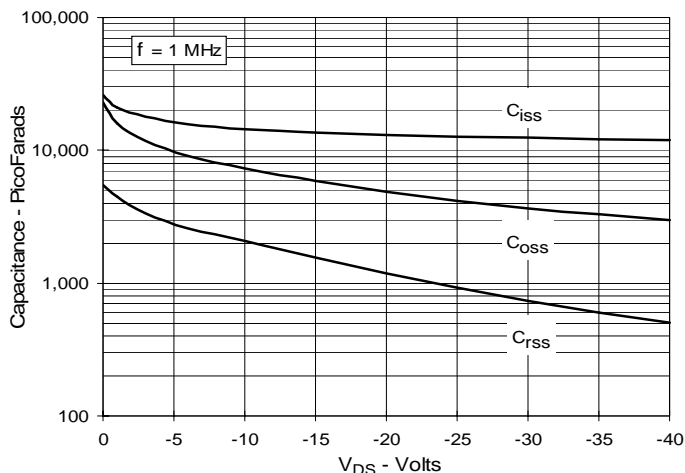
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**

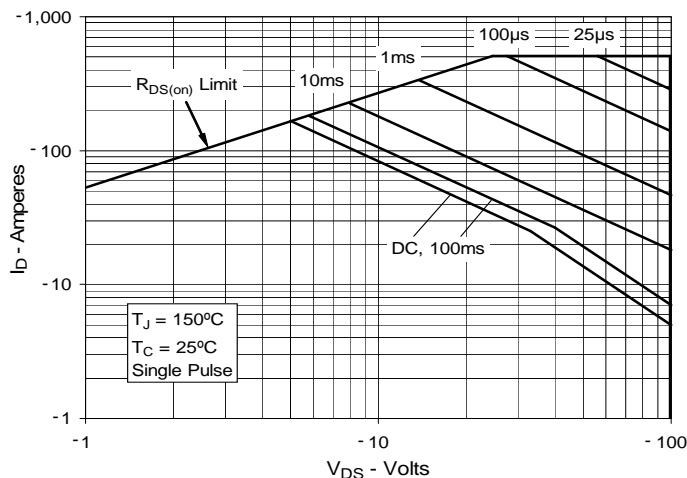


Fig. 13. Maximum Transient Thermal Impedance

